

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1336	365/158.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L2	1286	365/171.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L3	856	365/173.ccls.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L4	13	oh-hyung-rok.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L5	21	cho-woo-yeong.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:00
L6	3	kim-su-yeon.in.	US-PGPUB; USPAT	OR	ON	2006/01/31 13:01

Day : Tuesday  
Date: 1/31/2006


**PALM INTRANET**

Time: 13:02:54

**Inventor Name Search Result**

Your Search was:

Last Name = OH

First Name = HYUNG-ROK

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">10660802</a>	<a href="#">6853599</a>	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	OH, HYUNG-ROK
<a href="#">10805696</a>	<a href="#">6943395</a>	150	03/22/2004	PHASE RANDOM ACCESS MEMORY WITH HIGH DENSITY	OH, HYUNG-ROK
<a href="#">10828894</a>	Not Issued	80	04/20/2004	Magnetic random access memory device	OH, HYUNG-ROK
<a href="#">10829807</a>	Not Issued	95	04/22/2004	WRITING DRIVER CIRCUIT OF PHASE-CHANGE MEMORY	OH, HYUNG-ROK
<a href="#">10921797</a>	<a href="#">6885602</a>	150	08/20/2004	PROGRAMMING METHOD OF CONTROLLING THE AMOUNT OF WRITE CURRENT APPLIED TO PHASE CHANGE MEMORY DEVICE AND WRITE DRIVER CIRCUIT THEREFOR	OH, HYUNG-ROK
<a href="#">10937943</a>	Not Issued	30	09/11/2004	Phase-change memory device and method that maintains the resistance of a phase-change material in a reset state within a constant resistance range	OH, HYUNG-ROK
<a href="#">10943300</a>	<a href="#">6982913</a>	150	09/17/2004	DATA READ CIRCUIT FOR USE IN A SEMICONDUCTOR MEMORY AND A METHOD THEREOF	OH, HYUNG-ROK
<a href="#">11079198</a>	Not Issued	41	03/15/2005	Programming method of controlling the amount of write current applied to phase change memory device and write driver circuit therefor	OH, HYUNG-ROK
<a href="#">11177115</a>	Not Issued	30	07/08/2005	Phase random access memory with high density	OH, HYUNG-ROK

<a href="#">11220294</a>	Not Issued	30	09/06/2005	Semiconductor memory device capable of compensating for leakage current	OH, HYUNG-ROK
<a href="#">11249858</a>	Not Issued	20	10/13/2005	Data read circuit for use in a semiconductor memory and a method therefor	OH, HYUNG-ROK
<a href="#">11253626</a>	Not Issued	20	10/20/2005	Semiconductor memory device	OH, HYUNG-ROK
<a href="#">11260602</a>	Not Issued	30	10/27/2005	Magneto-resistive RAM having multi-bit cell array structure	OH, HYUNG-ROK

Inventor Search Completed: No Records to Display.


**Search Another: Inventor**

Last Name	First Name	
<input type="text" value="oh"/>	<input type="text" value="hyung-rok"/>	<input type="button" value="Search"/>

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Day : Tuesday  
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**PALM INTRANET**

Time: 13:03:39

**Inventor Name Search Result**

Your Search was:

Last Name = CHO

First Name = WOO-YEONG

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">09955458</a>	Not Issued	71	09/18/2001	Reference voltage generating circuit using active resistance device	CHO, WOO-YEONG
<a href="#">10660802</a>	<a href="#">6853599</a>	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	CHO, WOO-YEONG
<a href="#">10773901</a>	Not Issued	93	02/06/2004	DEVICE AND METHOD FOR PULSE WIDTH CONTROL IN A PHASE CHANGE MEMORY DEVICE	CHO, WOO-YEONG
<a href="#">10805696</a>	<a href="#">6943395</a>	150	03/22/2004	PHASE RANDOM ACCESS MEMORY WITH HIGH DENSITY	CHO, WOO-YEONG
<a href="#">10828894</a>	Not Issued	80	04/20/2004	Magnetic random access memory device	CHO, WOO-YEONG
<a href="#">10829807</a>	Not Issued	95	04/22/2004	WRITING DRIVER CIRCUIT OF PHASE-CHANGE MEMORY	CHO, WOO-YEONG
<a href="#">10921797</a>	<a href="#">6885602</a>	150	08/20/2004	PROGRAMMING METHOD OF CONTROLLING THE AMOUNT OF WRITE CURRENT APPLIED TO PHASE CHANGE MEMORY DEVICE AND WRITE DRIVER CIRCUIT THEREFOR	CHO, WOO-YEONG
<a href="#">10937943</a>	Not Issued	30	09/11/2004	Phase-change memory device and method that maintains the resistance of a phase-change material in a reset state within a constant resistance range	CHO, WOO-YEONG
<a href="#">10943300</a>	<a href="#">6982913</a>	150	09/17/2004	DATA READ CIRCUIT FOR USE IN A SEMICONDUCTOR MEMORY AND A METHOD THEREOF	CHO, WOO-YEONG

<a href="#">10976626</a>	Not Issued	41	10/29/2004	Nonvolatile semiconductor memory device with scalable two transistor memory cells	CHO, WOO-YEONG
<a href="#">11074557</a>	Not Issued	30	03/08/2005	Phase change memories and/or methods of programming phase change memories using sequential reset control	CHO, WOO-YEONG
<a href="#">11079198</a>	Not Issued	41	03/15/2005	Programming method of controlling the amount of write current applied to phase change memory device and write driver circuit therefor	CHO, WOO-YEONG
<a href="#">11092456</a>	Not Issued	30	03/29/2005	Phase-change memory element driver circuits using measurement to control current and methods of controlling drive current of phase-change memory elements using measurement	CHO, WOO-YEONG
<a href="#">11124341</a>	Not Issued	20	05/06/2005	Control of set/reset pulse in response to peripheral temperature in PRAM device	CHO, WOO-YEONG
<a href="#">11177115</a>	Not Issued	30	07/08/2005	Phase random access memory with high density	CHO, WOO-YEONG
<a href="#">11184184</a>	Not Issued	25	07/19/2005	Phase change memory device for use in a burst read operation and a data reading method thereof	CHO, WOO-YEONG
<a href="#">11249858</a>	Not Issued	20	10/13/2005	Data read circuit for use in a semiconductor memory and a method therefor	CHO, WOO-YEONG
<a href="#">11260602</a>	Not Issued	30	10/27/2005	Magneto-resistive RAM having multi-bit cell array structure	CHO, WOO-YEONG
<a href="#">11303910</a>	Not Issued	20	12/19/2005	Phase change memory device and method of driving word line thereof	CHO, WOO-YEONG
<a href="#">11316256</a>	Not Issued	20	12/23/2005	Phase change random access memory device having variable drive voltage circuit	CHO, WOO-YEONG

Inventor Search Completed: No Records to Display.

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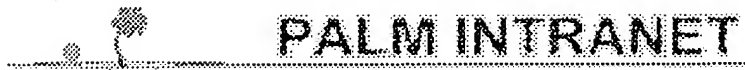
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## Inventor Name Search Result

Your Search was:

Last Name = KIM

First Name = SU-YEON

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10660802</u>	6853599	150	09/12/2003	MAGNETIC MEMORY DEVICE IMPLEMENTING READ OPERATION TOLERANT TO BITLINE CLAMP VOLTAGE (VREF)	KIM, SU-YEON
<u>10828894</u>	Not Issued	80	04/20/2004	Magnetic random access memory device	KIM, SU-YEON

Inventor Search Completed: No Records to Display.

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